

# Characterizing MBE grown SrMoO 3 thin films as a transparent conductor

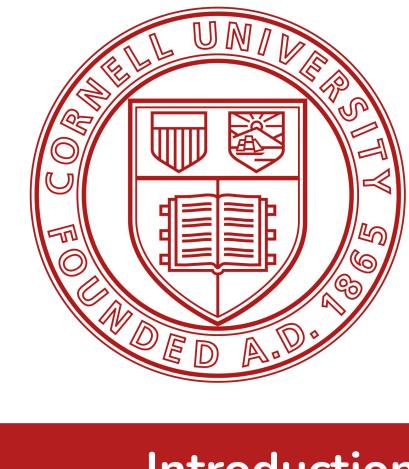
PARTNERSHIPS FOR RESEARC



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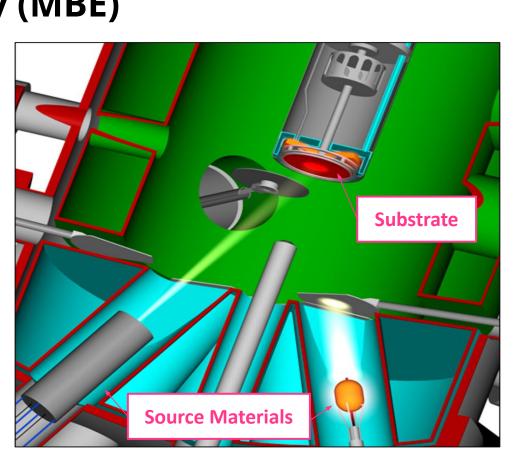
### Introduction of SrMoO<sub>2</sub> SrMoO<sub>3</sub> is the most conducting perovskite oxide and also optically transparent. As a result, it is categorized as a Transparent Conducting Oxide SrMoO3 s.c. (TCO) and suitable as a transparent bottom electrode for other perovskites. lattice constant a (Å) P. Salg et al. APL Mater. **7**, 051107 (2019). Metals have good electrical conductivity but are opaque. Degenerately doped semiconductors are optically transparent but have low electrical conductivity Correlated metals like SrMoO<sub>3</sub> are both transparent and good conductors.

#### Methodology

#### Molecular-Beam Epitaxy (MBE)

 $\omega_{\rm p} = \sqrt{(e^2/\epsilon_0 \epsilon_{\rm r})(n/m^*)}$  (eV)

SrMoO<sub>3</sub> thin films were grown using MBE, a deposition technique that uses molecular beams from a heated source in ultra-high vacuum. MBE provides flexibility and unparalleled control over growth parameters.



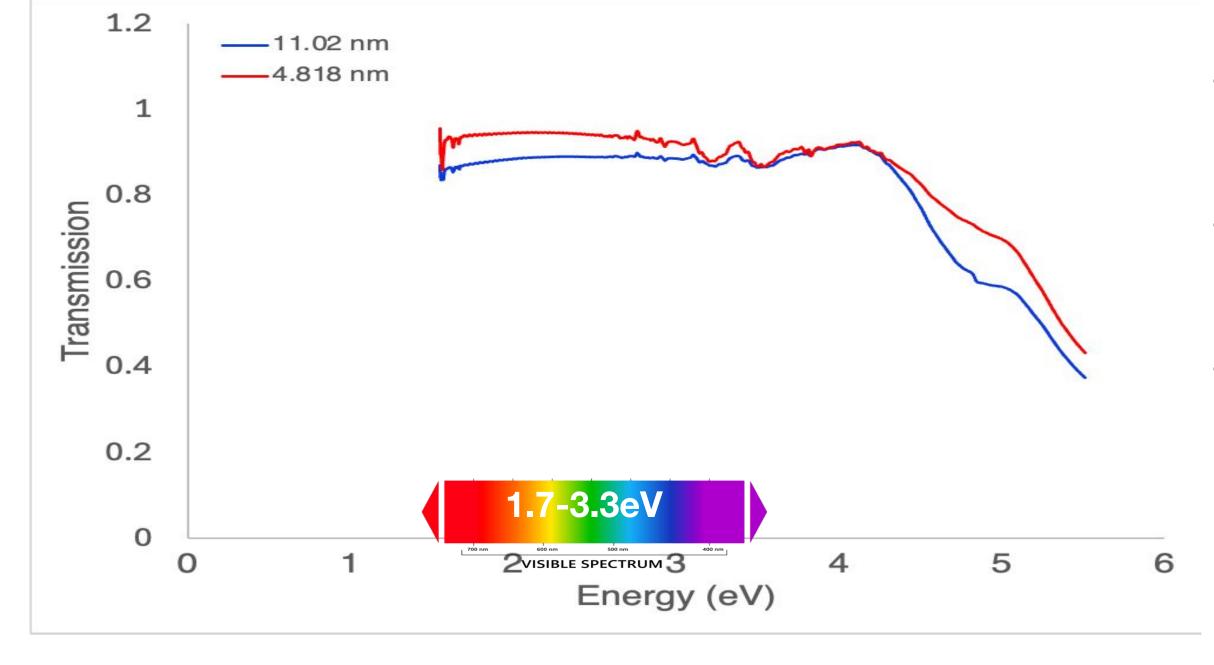
| Growth Parameters     |  |
|-----------------------|--|
| Substrate temperature | 1250 ℃   |
| Sources               | Sr, MoO <sub>3</sub>   |
| Background Pressure   | 5 x 10 <sup>-8</sup> torr (2 x 10 <sup>-8</sup> from leak valve) |
| Substrate             | DyScO <sub>3</sub> (110)   |
| Lattice Mismatch      | 0.3% compressive   |

#### Results **Structural Characterization - X-Ray Diffraction** 2Θ-ω scans ★ DyScO<sub>3</sub> Phase pure SrMoO<sub>3</sub> films of varying thicknesses were grown on DyScO<sub>3</sub> substrates. All films were grown at 1250 12.7 nm °C, in a Sr excess regime. Fringes indicate sharp interface between film and 11.0 nm substrate, as well as good 10.4 nm crystalline quality. Peak around 40° (Orange 4.8 nm curve) is Molybdenum metal, formed possibly due to source instability. $2\theta$ (Degrees) **Transport- Resistivity vs. Temperature** 65 - 4.8 nm Residual Resistivity Ratio (RRR) — 11.0 nm Ratio of a material's resistivity at room temperature to its resistivity at low temperatures Higher the RRR = less defects in measured as the sample. RRR is record for SrMoO<sub>3</sub> thin

160 200 240 280

Temperature (K)

## **Optical Characterization - UV-Vis Spectroscopy**



 The thinner film exhibits a higher transmission than the

background pressures.

films, but has higher room

→ Future work= Improve on these

results by improving stability of

MoO<sub>3</sub> source and grow in lower

temperature resistivity

compared to those in

literature.

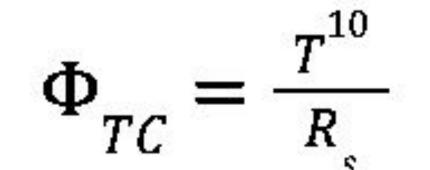
 Films are optically transparent within visible regime.

thicker film.

 In the future, we hope to simulate the optical spectra of SrMoO<sub>3</sub> and measure other energy regimes.

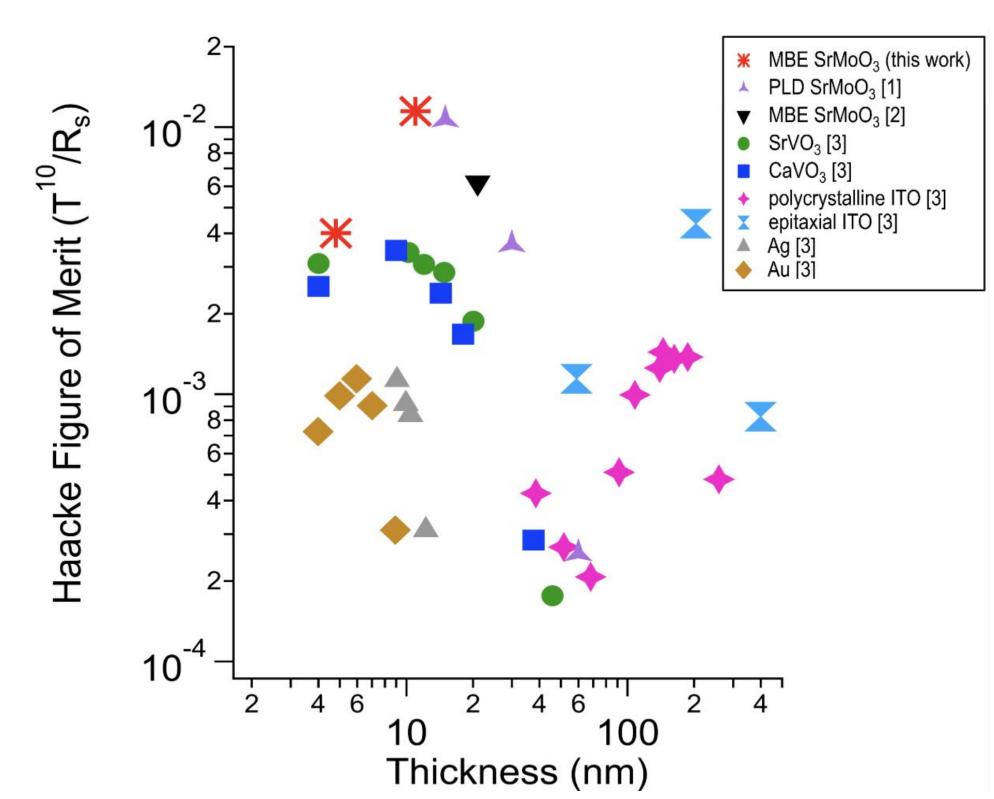
#### Conclusions

#### Haack Figure of Merit (FOM):



T- transmission at 550
nm

Higher the Haacke FOM = better TCO.



#### Conclusions

- Successfully grew SrMoO<sub>3</sub> thin films by MBE.
- Our best film had a RRR of 9.4 and room temperature resistivity of 30  $\mu\Omega$ -cm.
- Our SrMoO<sub>3</sub> films have a high Haacke FOM, further validating that SrMoO<sub>3</sub> is a promising TCO.

In the future, we aim to compare more SrMoO<sub>3</sub> Haacke FOM to other correlated metal oxides.

#### Acknowledgments

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#### References

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- [3] Kuznetsova et al. *J. Vac. Sci. Technol. A* **41**, 053412-8 (2023).